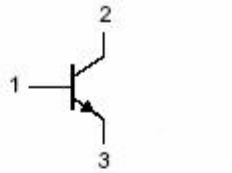
isc Silicon NPN Power Transistor — 2SC2528



PIN 1. BASE
2.COLLECTOR
3. EMITTER
TO-220C package

DESCRIPTION

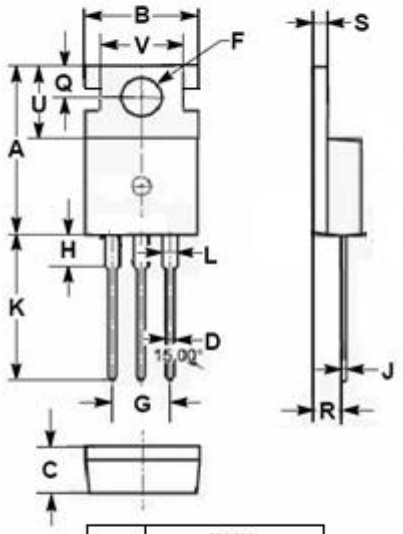
- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= 120V(Min)
- Low Collector-Emitter Saturation Voltage-
  : $V_{CE(sat)}$= 1.0V(Max) @I_C= 0.7A
- Complement to Type 2SA1078
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- High frequency power amplifier,
  Audio power amplifier
  Dirvers

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	120	V
V_{CEO}	Collector-Emitter Voltage	120	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	2.0	A
P_C	Collector Power Dissipation @ T_C=25℃	25	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃



DIM	mm MIN	MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 1mA ; I_B= 0	120			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 1mA ; I_C= 0	6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 0.7A; I_B= 0.07A			1.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= 0.7A ; V_{CE}= 5V			1.7	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 120V ; I_E= 0			1	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 6V ; I_C= 0			1	μA
h_{FE-1}	DC Current Gain	I_C= 0.3A ; V_{CE}= 5V	60		350	
h_{FE-2}	DC Current Gain	I_C= 0.7A ; V_{CE}= 5V	50			
f_T	Current-Gain—Bandwidth Product	I_C= 0.5A; V_{CE}= 10V;f_{test}= 10MHz		60		MHz
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= 20V;f_{test}= 1.0MHz		60		pF